Zibo Seno Electronic Engineering Co., Ltd.



MBRF2040 CT - MBRF20200CT



ITO-220AB

Min

14.50



Max

15.50

20.0A SCHOTTKY BARRIER DIODE

Dim

Α

Features

- Schottky Barrier Chip
- Ideally Suited for Automatic Assembly
- Low Power Loss, High Efficiency
- For Use in Low Voltage Application
- Guard Ring Die Construction
- Plastic Case Material has UL Flammability Classification Rating 94V-O

Mechanical Data

Case: ITO-220AB, Molded Plastic

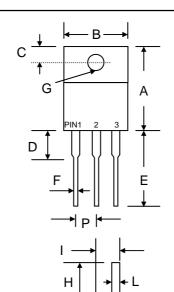
Terminals: Plated Leads Solderable per

MIL-STD-202, Method 208

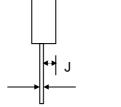
Polarity: See Diagram

Mounting Position: Any

• Lead Free: For RoHS / Lead Free Version



В	9.50	10.50			
С	2.55	2.90			
D	3.30	4.30			
E	13.00	14.00			
F	0.30	0.90			
G	3.00 Ø	3.80 Ø			
Н	6.30	7.30			
ı	4.20	4.80			
J	2.50	2.90			
K	0.47	0.75			
L	2.50	3.10			
Р	2.35	2.75			
All Dimensions in mm					
•		•			



PIN 1 -	0—	-	+
PIN 3 -	<u> </u>	-	O PIN 2

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	MBRF 2040 CT	MBRF 2045 CT	MBRF 2050 CT	MBRF 2060 CT	MBRF 20100 CT	MBRF 20150 CT	MBRF 20200 CT	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	VRRM VRWM VR	40	45	50	60	100	150	200	V
RMS Reverse Voltage	VR(RMS)	28	31	35	42	70	105	140	V
Average Rectified Output Current @T _L = 75°C (Note 1)	lo	20.0					Α		
Non-Repetitive Peak Forward Surge Current 8.3m Single half sine-wave superimposed on rated load (JEDEC Method)	S IFSM	150					А		
Forward Voltage @I _F = 10A	VFM	0.70		0.80		0.85		0.92	V
Peak Reverse Current $@T_A = 25^{\circ}C$ At Rated DC Blocking Voltage $@T_A = 100^{\circ}C$	I IDM	0.1 20					mA		
Typical Junction Capacitance (Note 2)	Cj	350 280		30	200			pF	
Typical Thermal Resistance (Note 1)	$R_{ heta}$ JA	3.0 2.0				°C/W			
Operating and Storage Temperature Range	Тj, Tsтg	-55 to +150 -55 to +179				+175	°C		

Note: 1. Valid provided that leads are kept at ambient temperature at a distance of 9.5mm from the case.

2. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

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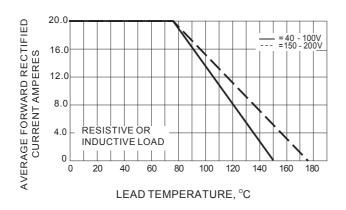


Fig.1- FORWARD CURRENT DERATING CURVE

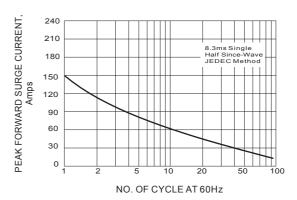


Fig.2- MAXIMUM NON - REPETITIVE SURGE **CURRENT**

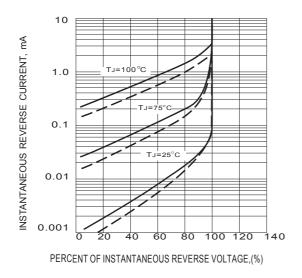


Fig.3- TYPICAL REVERSE CHARACTERISTICS

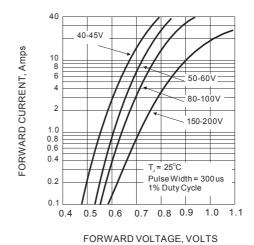


Fig.4-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS